



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/470,650

Filed: December 22, 1999

## Title: USE OF A PLASMA SOURCE TO FORM A LAYER DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

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Commissioner for Patents  
P.O. Box 1450  
Washington, D.C. 20231

Dear Sir:

Applicants herein respond to the Office Action dated June 8, 2003. Please amend the above-captioned application as follows.

## IN THE CLAIMS

**“Certificate of Mailing”**

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on:

Date 7/15/03

Signature

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prejudice.

Please amend the claims to the form indicated below.

11. (Office amended) A method of processing a semiconductor device, comprising:

providing a first protruding feature on a layer of said semiconductor device;

providing a second protruding feature on said layer;

defining a recess between said first protruding feature and said second protruding feature; and

plasma-depositing a material within said recess, wherein said step of plasma-

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